

## Silicon NPN Power Transistors

2SC4430

## DESCRIPTION

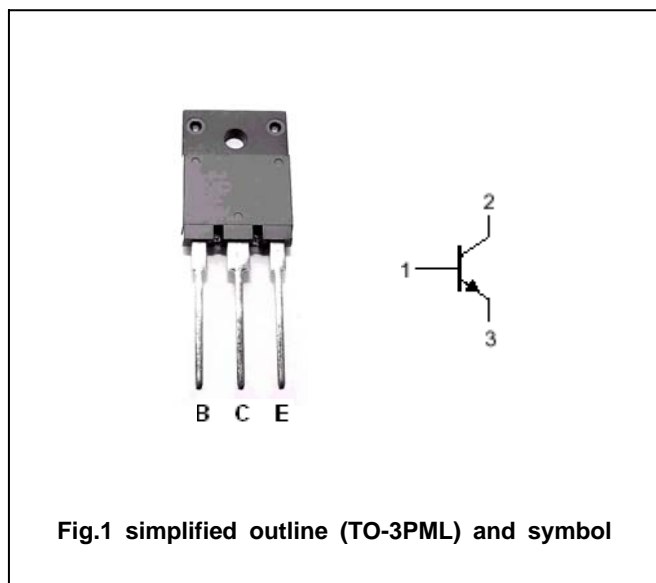
- With TO-3PML package
- High breakdown voltage, high reliability.
- Fast switching speed.
- Wide area of safe operation

## APPLICATIONS

- Switching regulator applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings( $T_c=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	1100	V
$V_{CEO}$	Collector-emitter voltage	Open base	800	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		12	A
$I_{CM}$	Collector current-peak		30	A
$I_B$	Base current		6	A
$P_C$	Collector power dissipation	$T_c=25^\circ\text{C}$	65	W
			3	
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA; I <sub>E</sub> =0	1100			V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =5mA; R <sub>BE</sub> =∞	800			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =6A; I <sub>B</sub> =1.2A			2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =6A; I <sub>B</sub> =1.2A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =800V; I <sub>E</sub> =0			10	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.8A; V <sub>CE</sub> =5V	10		40	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =4A; V <sub>CE</sub> =5V	8			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.8A; V <sub>CE</sub> =10V		15		MHz
C <sub>OB</sub>	Output capacitance	V <sub>CB</sub> =10V; f=1MHz		215		pF

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =8A; R <sub>L</sub> =50 Ω I <sub>B1</sub> =1.6A; - I <sub>B2</sub> =3.2A V <sub>CC</sub> =400V			0.5	μ s
t <sub>stg</sub>	Storage time				3.0	μ s
t <sub>f</sub>	Fall time				0.3	μ s

◆ h<sub>FE-1</sub> classifications

K	L	M
10-20	15-30	20-40



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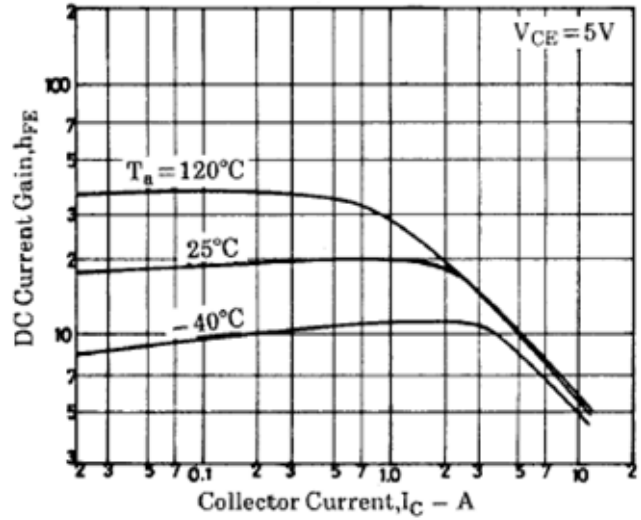
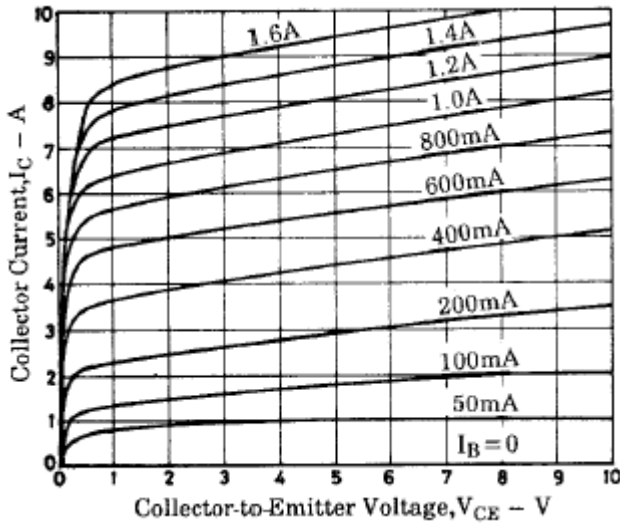


Fig.4 DC current Gain

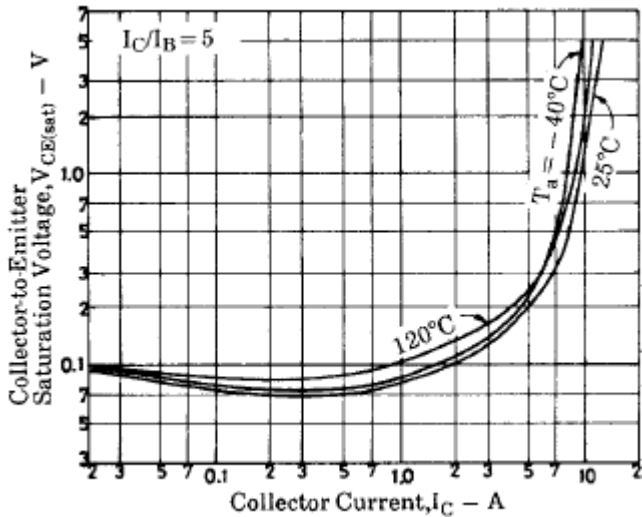


Fig.5 Collector-Emitter Saturation Voltage

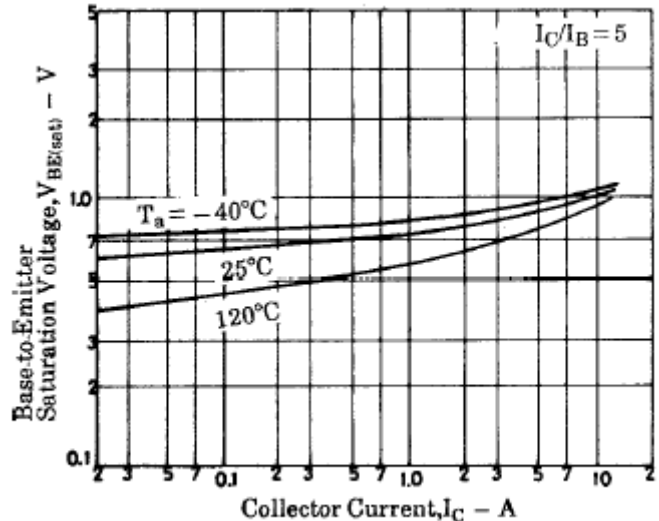


Fig.6 Base-Emitter Saturation Voltage

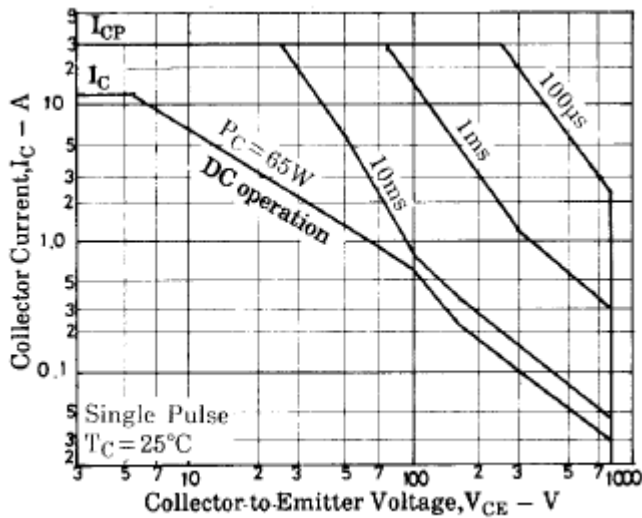


Fig.7 Safe Operating Area